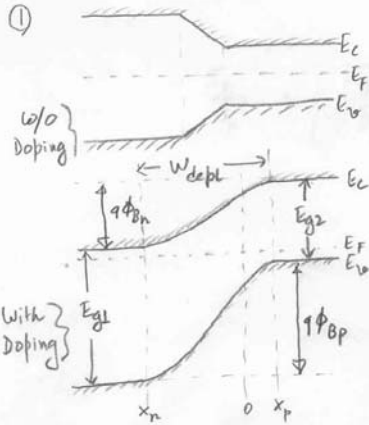


PROBLEM 1



Band Diagrams

$$\left. \begin{aligned} \epsilon_{Si} (\text{AlGaAs}) &= 13.1 \epsilon_0 \\ \epsilon_{Si} (\text{GaAs}) &= 11.9 \epsilon_0 \end{aligned} \right\} \text{Safe to assume } \epsilon_{S1} \approx \epsilon_{S2} = \epsilon_S$$

$$qV_{bi} \approx RT \ln \frac{N_A N_D}{n_i^2} + \Delta E_C \quad \text{if } N_{C1} \approx N_{C2}, N_{V1} \approx N_{V2}$$

$$W_{depl} \approx \left[\frac{2 \epsilon_S \left(\frac{1}{N_A} + \frac{1}{N_D} \right) (V_{bi} - \frac{2RT}{q}) \right]^{1/2}$$

$$= 480 \text{ nm} \quad (1.51 \text{ V})$$

Barrier for electrons

$$q\phi_{Bn} = qV_{bi} - \Delta E_C \quad \left\{ \begin{array}{l} \text{Since graded region} \\ \text{is n-doped, CB is flat +} \\ \text{VB has a field} \end{array} \right.$$

$$= 1.21 \text{ eV} \quad \text{lower than homojunction!}$$

Barrier for holes

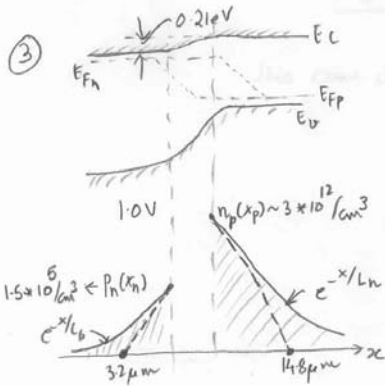
$$E_{g2} + q\phi_{BP} = E_{g1} + q\phi_{Bn} \quad (\text{see figure})$$

$$q\phi_{BP} = q\phi_{Bn} + (E_{g1} - E_{g2})$$

$$= 1.21 \text{ eV} + 0.5 \text{ eV} = 1.71 \text{ eV}$$

larger than homojunction!

$$\Rightarrow J_n \uparrow, J_p \downarrow !!$$



$$n_p(x) = n_p(x_p) e^{-x/L_n}$$

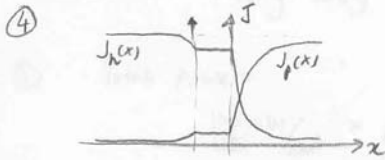
$$= \frac{n_i^2}{N_A} \exp\left(\frac{qV_A}{kT}\right) \approx 3 \times 10^{12} / \text{cm}^3$$

$$p_n(x_n) = \frac{n_i^2}{N_D} \exp\left(\frac{qV_A}{kT}\right) = \frac{n_i^2}{N_D} \exp\left(-\frac{\Delta E_g}{kT}\right) \exp\left(\frac{qV_A}{kT}\right)$$

$$\approx 1.5 \times 10^5 / \text{cm}^3$$

Problem 1 contd...

(2)



$$J_n(x_p) = \frac{-q D_n n_{p0}}{L_n} (e^{\frac{qV_A}{kT}} - 1) \approx -66 \text{ mA/cm}^2$$

$$J_p(x_n) = \frac{-q D_p p_{n0}}{L_p} (e^{\frac{qV_A}{kT}} - 1) \approx -0.6 \text{ nA/cm}^2$$

$$J_n(x_p) \gg J_p(x_n)$$

$$\frac{J_n}{J_p} = \left\{ \sqrt{\frac{D_n}{D_p}} \cdot \sqrt{\frac{\tau_p}{\tau_n}} \cdot \frac{N_D}{N_A} \right\} \cdot \exp\left(\frac{\Delta E_g}{kT}\right)$$

Homojunction

Heterojunction term

$$\frac{J_n}{J_p} \approx \boxed{0.46}$$

$$\text{leads to } \frac{J_n}{J_p} \approx \boxed{10^8}$$

Huge difference!!

(5)

If $t_{bx} > x_n$, only that part of the bandgap difference that lies in the depletion region contributes to $\exp\left(\frac{\Delta E_g}{kT}\right)$.

Effective ΔE_g is

$$\Delta E_g^{eff} = E_{g1}(x_n) - E_{g2}$$

This can lead to substantial drop in the ratio $\frac{J_n}{J_p}$.

PROBLEM 2

(Very Easy Problem)

3

⑥ Total power:

$$100 \text{ mW/cm}^2 * (4 * 1 \text{ cm}^2) * 5\% = \boxed{20 \text{ mW}}$$

⑦ EHPs/second -

$$\frac{20 \text{ mW} * 10\%}{\frac{1.424}{E_g} + \frac{1.6 * 10^{-19}}{e}} = \boxed{8.8 * 10^{15} \text{ EHPs/s}}$$

$$\therefore G_L = \frac{8.8 * 10^{15} \text{ EHPs/s}}{4 * 10^{-4} \text{ cm}^2} = \boxed{2.2 * 10^{19} / \text{cm}^2 \cdot \text{s}}$$

⑧ Short-circuit current is

$$I_L = q G_L (L_p + L_n) \cdot S \\ = \boxed{0.28 \text{ mA}}$$